

HAMADA - 09/663,340
Client/Matter: 020847-0271420

a plurality of second semiconductor regions of the second conductivity type having a second depth as measured from said major surface of the body region that is less than the first depth; and

a plurality of noncontiguous third semiconductor regions of the first conductivity type whose major extension is in a direction parallel to both the major surface of the body region and the trench gates;

wherein the body region is exposed between the plurality of second semiconductor regions and the second semiconductor regions connect the plurality of first semiconductor regions spaced apart from one another.

2. (Cancelled)

3. (Previously presented) A semiconductor device according to claim 1, wherein the first semiconductor regions are formed along the trench gates, and the second semiconductor regions connect the first semiconductor regions formed between the trench gates so as to form a ladder-shaped configuration.

4. (Cancelled)

5. (Original) A semiconductor device according to claim 1, further comprising a wiring member connected to at least one of the plurality of trench gates.

6. (Cancelled)

7. (Original) A semiconductor device according to claim 3, further comprising a wiring member connected to at least one of the plurality of trench gates.

8. (Cancelled)

9. (Original) A semiconductor device according to claim 1, further comprising a wiring member connected to the body region and to the second semiconductor region.

10. (Cancelled)

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11. (Original) A semiconductor device according to claim 3, further comprising a wiring member connected to the body region and to the second semiconductor region.

12-20. (Cancelled)